

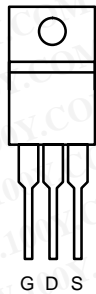


N-Channel 60-V (D-S), 175°C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
60	0.018	60

**175°C Rated**  
Maximum Junction Temperature  
**TrenchFET®**  
Power MOSFETs

TO-220AB

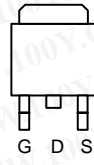


Top View

SUP60N06-18

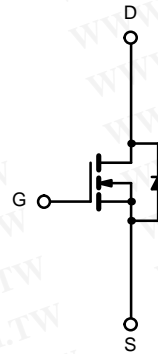
DRAIN connected to TAB

TO-263



Top View

SUB60N06-18



N-Channel MOSFET

勝特力材料 886-3-5753170  
勝特力电子(上海) 86-21-54151736  
勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175^\circ\text{C}$ )	$T_C = 25^\circ\text{C}$	$I_D$	60	A
	$T_C = 100^\circ\text{C}$		39	
Pulsed Drain Current		$I_{DM}$	120	
Avalanche Current		$I_{AR}$	60	
Repetitive Avalanche Energy <sup>a</sup>	L = 0.1 mH	$E_{AR}$	180	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$ (TO-220AB and TO-263)	$P_D$	120 <sup>b</sup>	W
	$T_A = 25^\circ\text{C}$ (TO-263) <sup>c</sup>		3.7	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-263) <sup>c</sup>	$R_{thJA}$	40	$^\circ\text{C}/\text{W}$
	Free Air (TO-220AB)		62.5	
Junction-to-Case		$R_{thJC}$	1.25	

Notes:

- a. Duty cycle  $\leq 1\%$ .
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>



SPECIFICATIONS (T <sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = 1 mA	2.0		4.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	60			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A		0.014	0.018	Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C		0.024	0.030	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C		0.031	0.036	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		49		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		2000		pF
Output Capacitance	C <sub>oss</sub>			400		
Reverse Transfer Capacitance	C <sub>rss</sub>			115		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 60 A		39	60	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			12		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			10		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 0.5 Ω I <sub>D</sub> = 60 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω		12	30	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			11	30	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			25	50	
Fall Time <sup>c</sup>	t <sub>f</sub>			15	30	
<b>Source-Drain Diode Ratings and Characteristics (T<sub>C</sub> = 25 °C)<sup>b</sup></b>						
Continuous Current	I <sub>s</sub>				60	A
Pulsed Current	I <sub>SM</sub>				120	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 60 A, V <sub>GS</sub> = 0 V			1.6	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 60 A, di/dt = 100 A/μs		60		ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			6.0		A
Reverse Recovery Charge	Q <sub>rr</sub>			0.4		μC

Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

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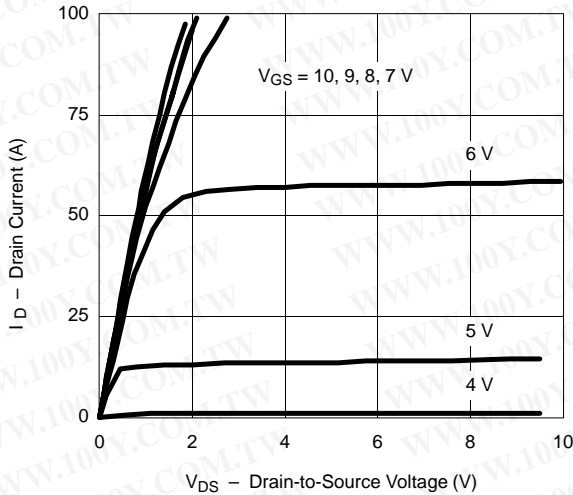
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**SUP/SUB60N06-18**

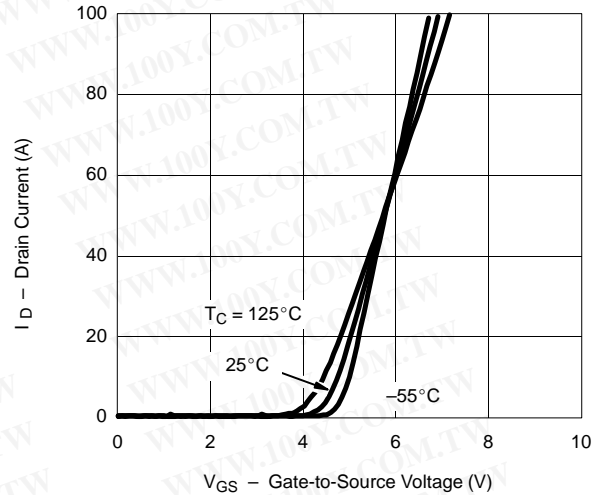
**Vishay Siliconix**

**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

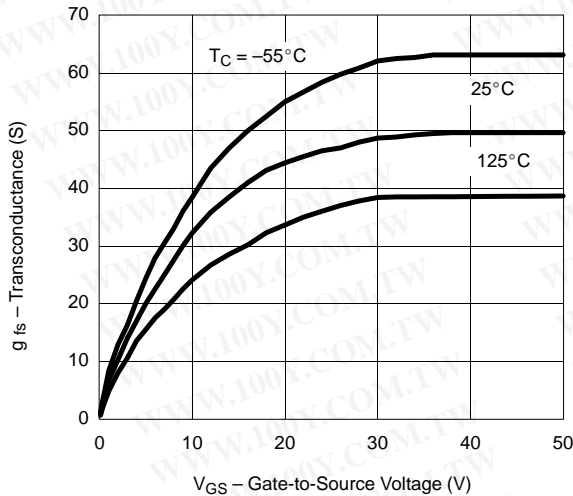
**Output Characteristics**



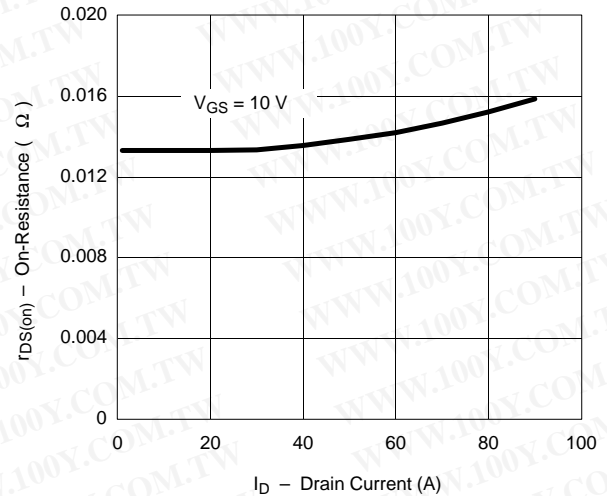
**Transfer Characteristics**



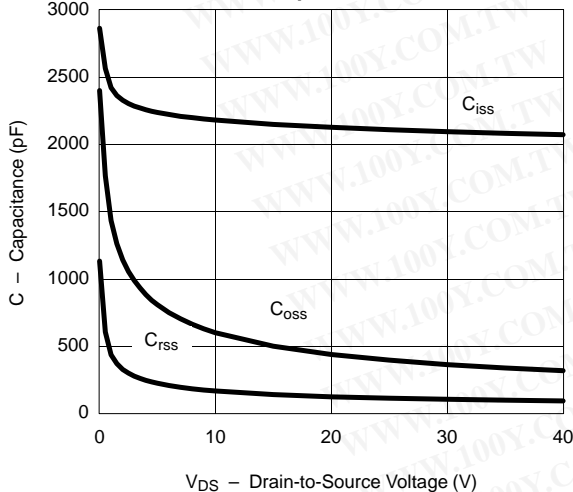
**Transconductance**



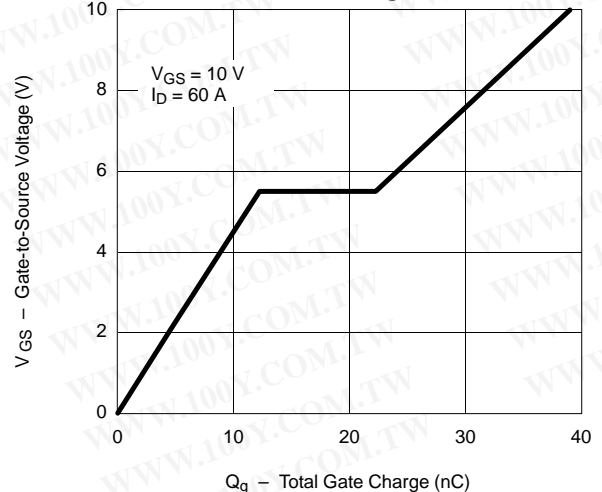
**On-Resistance vs. Drain Current**



**Capacitance**

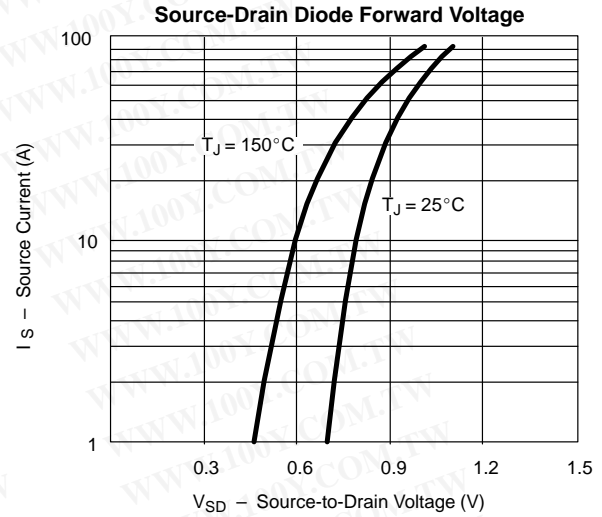
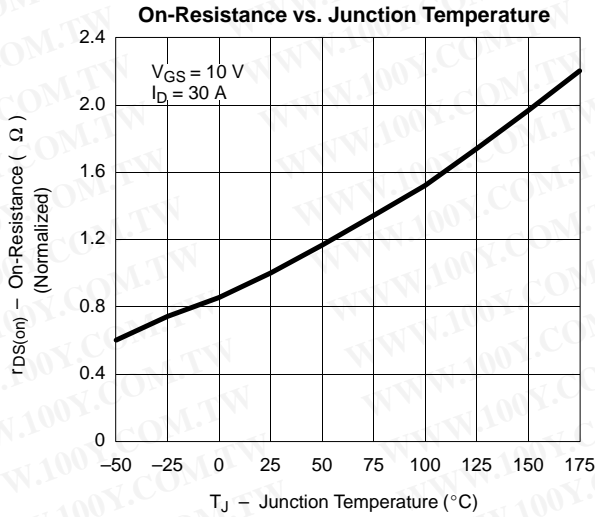


**Gate Charge**





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



**THERMAL RATINGS**

